



SOT-23 Plastic-Encapsulated Diodes

MMBD914LT1 SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^\circ\text{C}$)

Forward Current

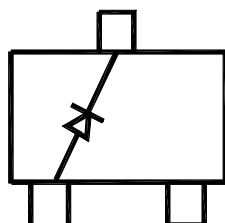
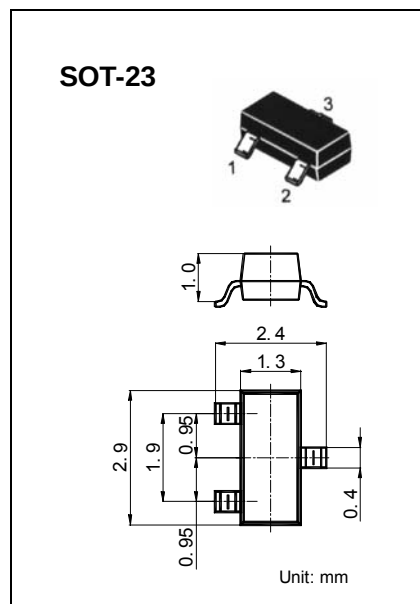
I_F : 200 mA

Reverse Voltage

V_R : 75 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$



Marking 5D

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R=75\text{V}$		2.5	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		20	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}$ $V_R=5\text{V}$ $R_C=100\Omega$		4	nS